

General Description

The 25N06 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

Features

- N-channel-Enhancement mode
- Lower On-resistance
- 100% Avalanche Tested
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current	25	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current	16	A
I_{DM}	Pulsed Drain Current	100	A
EAS	Single Pulse Avalanche Energy ¹	30	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	50	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ²	---	60	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction -Case	---	3	$^\circ\text{C/W}$

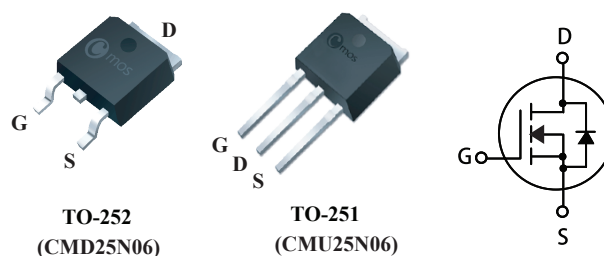
Product Summary

BVDSS	RDSON	ID
60V	33m Ω	25A

Applications

- DC-DC & DC-AC Converters
- Motor Control, Audio Amplifiers
- High Current, High Speed Switching
- Solenoid And Relay Drivers

TO-252 / 251 Pin Configuration



Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=20A$	---	29	33	m Ω
		$V_{GS}=4.5V$, $I_D=10A$	---	34	40	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=60V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=60V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=20A$	---	7	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1.2	---	Ω
Q_g	Total Gate Charge	$V_{DS}=30V$, $V_{GS}=10V$, $I_D=25A$	---	26	---	nC
Q_{gs}	Gate-Source Charge		---	8	---	
Q_{gd}	Gate-Drain Charge		---	5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V$, $V_{GEN}=10V$, $R_L=1.2\Omega$ $I_D=25A$, $R_G=7.5\Omega$	---	10	---	ns
T_r	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	30	---	
T_f	Fall Time		---	10	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1000	---	pF
C_{oss}	Output Capacitance		---	50	---	
C_{rss}	Reverse Transfer Capacitance		---	40	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	25	A
I_{SM}	Pulsed Source Current		---	---	100	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=30A$, $T_J=25^{\circ}\text{C}$	---	0.92	1.3	V

Note :

1. The EAS data shows Max. rating . The test condition is $V_{DS}=30V$, $V_{GS}=10V$, $L=0.5\text{mH}$, $I_{AS}=11A$.
2. Surface mounted on 1" x 1" FR4 Board.

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Typical Characteristics

